

Silicon NPN Power Transistors

2SC3460

DESCRIPTION

- With TO-3PN package
- High breakdown voltage and high reliability.
- Fast switching speed
- Wide area of safe operation

APPLICATIONS

- 800V/6A switching regulator applications

PINNING

| PIN | DESCRIPTION |
|-----|--------------------------------------|
| 1 | Base |
| 2 | Collector;connected to mounting base |
| 3 | Emitter |

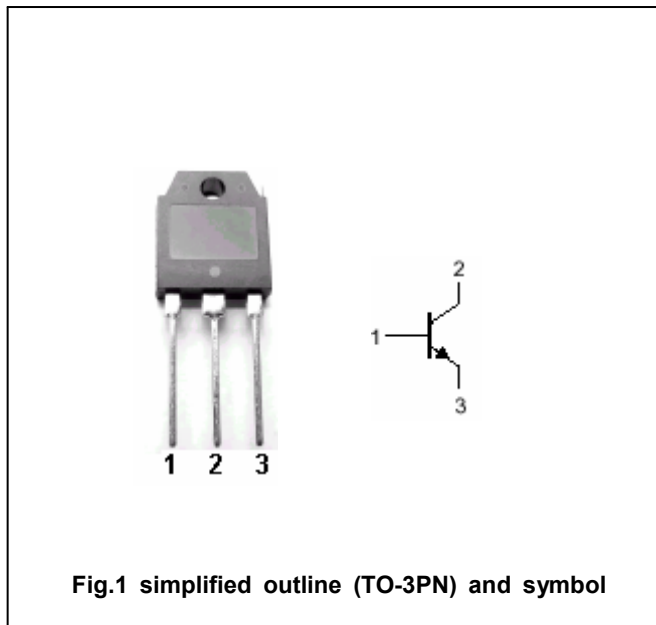


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=□)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|------------------|-----------------------------|---------------------|---------|------|
| V _{CBO} | Collector-base voltage | Open emitter | 1100 | V |
| V _{CEO} | Collector-emitter voltage | Open base | 800 | V |
| V _{EBO} | Emitter-base voltage | Open collector | 7 | V |
| I _C | Collector current | | 6 | A |
| I _{CM} | Collector current-peak | | 20 | A |
| I _B | Base current | | 3 | A |
| P _C | Collector power dissipation | T _C =25□ | 100 | W |
| T _j | Junction temperature | | 150 | □ |
| T _{stg} | Storage temperature | | -55~150 | □ |

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CHARACTERISTICS

T_j=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|---|------|------|-----|------|
| V _{(BR)CEO} | Collector-emitter breakdown voltage | I _C =5mA ; R _{BE} =∞ | 800 | | | V |
| V _{(BR)CBO} | Collector-base breakdown voltage | I _C =1mA ; I _E =0 | 1100 | | | V |
| V _{(BR)EBO} | Emitter-base breakdown voltage | I _E =1mA ; I _C =0 | 7 | | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =3A ; I _B =0.6A | | | 2.0 | V |
| V _{BEsat} | Base-emitter saturation voltage | I _C =3A ; I _B =0.6A | | | 1.5 | V |
| I _{CBO} | Collector cut-off current | V _{CB} =800V ; I _E =0 | | | 10 | μA |
| I _{EBO} | Emitter cut-off current | V _{EB} =5V ; I _C =0 | | | 10 | μA |
| h _{FE-1} | DC current gain | I _C =0.4A ; V _{CE} =5V | 10 | | 40 | |
| h _{FE-2} | DC current gain | I _C =2A ; V _{CE} =5V | 8 | | | |
| C _{ob} | Output capacitance | I _E =0 ; V _{CB} =10V ; f=1MHz | | 120 | | pF |
| f _T | Transition frequency | I _C =0.4A ; V _{CE} =10V | | 15 | | MHz |

Switching times

| | | | | | | |
|------------------|--------------|--|--|--|-----|----|
| t _{on} | Turn-on time | I _C =4A ; R _L =100Ω I _{B1} =0.8A ; I _{B2} =-1.6A V _{CC} =400V | | | 0.5 | μs |
| t _{stg} | Storage time | | | | 3.0 | μs |
| t _f | Fall time | | | | 0.3 | μs |

◆ h_{FE-1} Classifications

| K | L | M |
|-------|-------|-------|
| 10-20 | 15-30 | 20-40 |

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PACKAGE OUTLINE

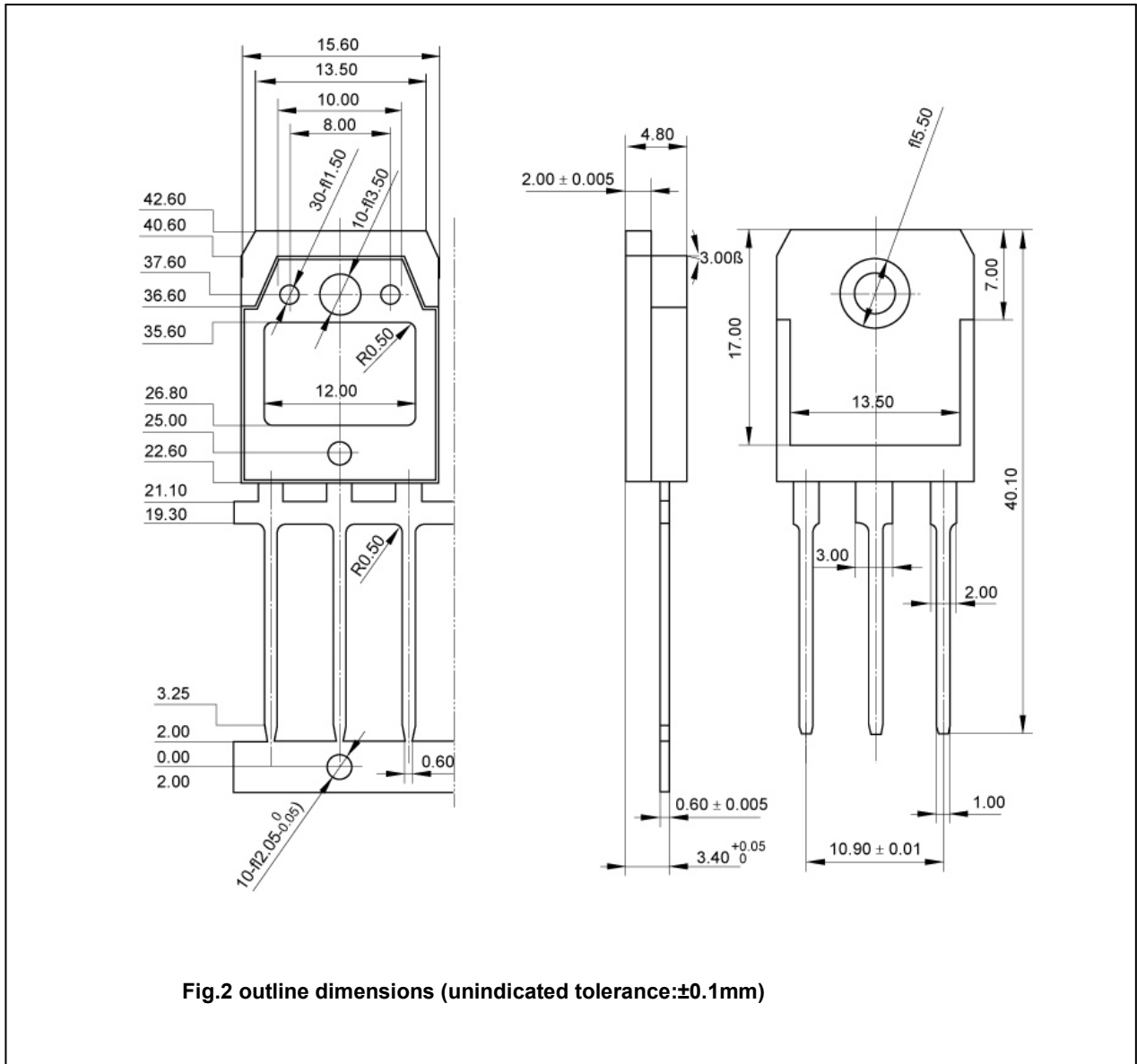


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)

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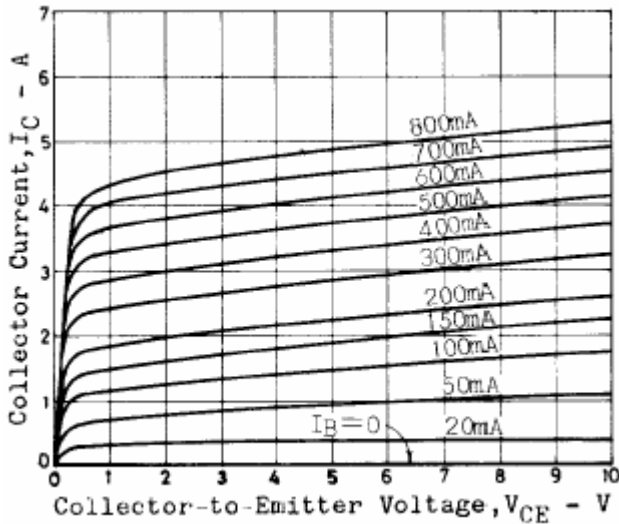


Fig.3 Static Characteristic

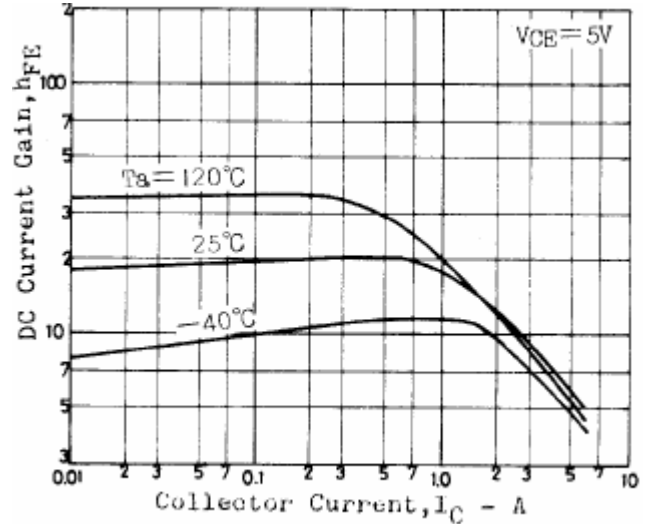


Fig.4 DC current Gain

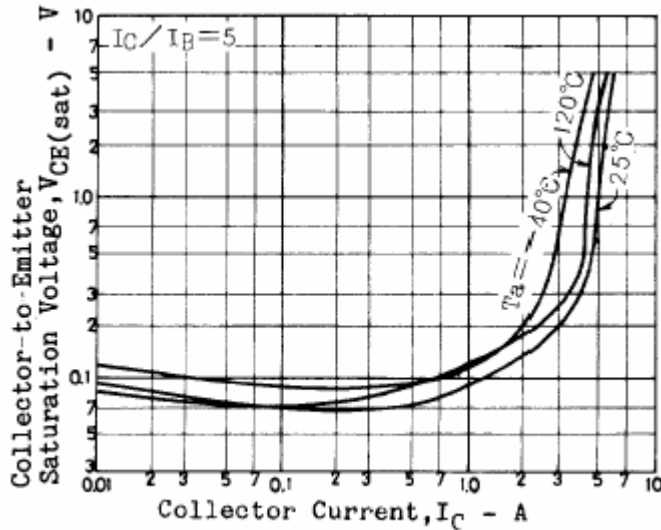


Fig.5 Collector-Emmitter Saturation Voltage

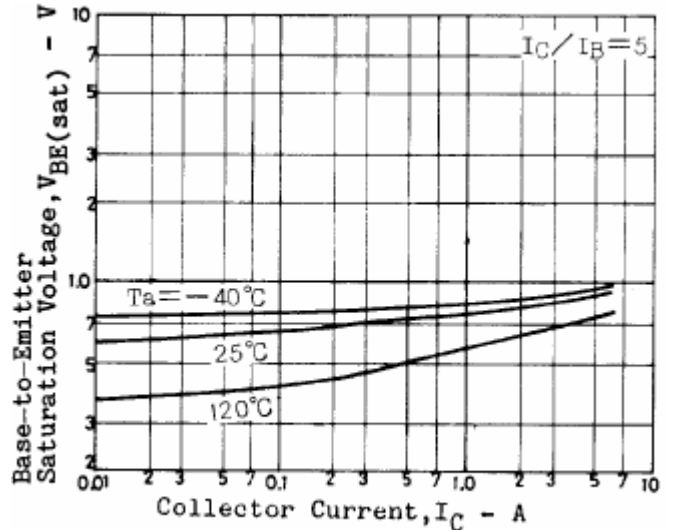


Fig.6 Base-Emmitter Saturation Voltage

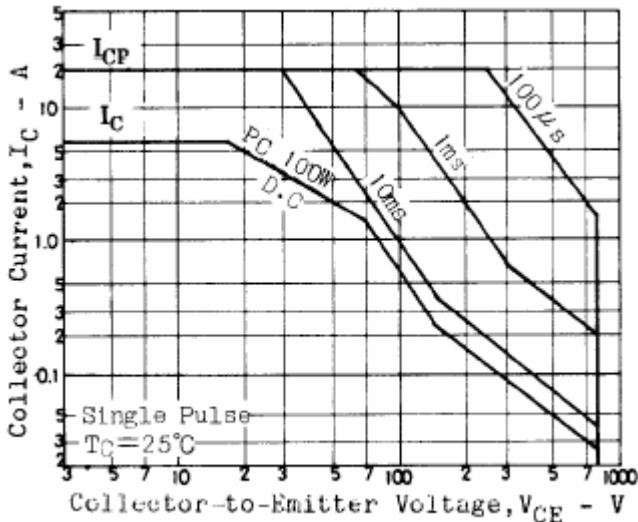


Fig.7 Safe Operating Area